

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	110	<pre>(("6784072") or ("6404014") or ("6429488") or ("6486037") or ("6602757") or ("6495429") or ("6593205") or ("6812114") or ("6743651") or ("6756639") or ("6835983") or ("6989058") or ("7084460") or ("6888221") or ("7075150") or ("6967376") or ("7067371") or ("7115463") or ("7141457") or ("5188978") or ("5767549") or ("6214694") or ("6255145") or ("6180486") or ("6426252") or ("6566177") or ("6222253") or ("6300218") or ("6432754") or ("7656257") or ("6043166") or ("5930643") or ("6090689") or ("6259137") or ("6204546") or ("6333532") or ("6846727") or ("6541356") or ("6805962") or ("6841457") or ("6946373") or ("6800518") or ("6717217") or ("6855436") or ("7049660") or ("7026249") or ("7169226") or ("7124558") or ("6861158") or ("7074686") or ("6991998") or ("7172930") or ("7141115") or ("7084050")) .PN.</pre>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 09:24
2	L3	43	L1 not L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 09:30
3	L2	67	L1 and ion near (implant\$7 bombard\$7 inject\$7 dope doping dopant oxygen "O. _{sub.2} " "B.u/c." Ga Al BF "BF. _{sub.2} " boron gallium aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 10:17

10/674,647 + 10/674,648

	L #	Hits	Search Text	DBs	Time Stamp
4	L4	2	L2 and (anodic anodization electrolytic)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:12
5	L5	2	L3 and (anodic anodization electrolytic)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:19
L21 L23 L24 L25 ←	L7	10676	((427/526,527,529,539,579,533) or (438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)).CCLS.	US - PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:08
7	L8	5312	(SOI GeSOI GSOI GeSiOI GESiOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum))	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:11
8	L9	3919	(Vacancies voids pores porous porosity damag\$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dope\$2)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:16
9	L10	66	L8 same L9	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:17

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	L #	Hits	Search Text	DBs	Time Stamp
10	L11	199	L8 and L9	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:17
11	L13	66	↓ L10 and L11	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:18
12	L15	133	L11 not L13	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:18
13	L16	1904	("HF.u/c." Hydrofluoric hydrofluoride Hydrofloric hydrofluoride Hydrofluoricacid hydrofluorideacid Hydro adj (fluoride fluoric floric)) Same (anodic anodization electrolytic)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:26
14	L17	29	L13 and L16	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:38
15	L18	36	L15 and L16	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:39
16	L19	37	L13 not L17	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:39

L23
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 L26
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 L18 ←
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 L20
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 L25 ↘
 L28

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	L #	Hits	Search Text	DBs	Time Stamp
17	L20	97	L15 not L18	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:39
18	L21	1	L17 and L7	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:40
19	L22	28	L17 not L21	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:40
20	L23	1	L18 and L7	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
21	L24	1	L19 and L7	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
22	L25	4	L20 and L7	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
23	L26	35	L18 not L23	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41

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	L #	Hits	Search Text	DBs	Time Stamp
24	L27	36	L19 not L24	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
25	L28	93	L20 not L25	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:42